

L Number	Hits	Search Text	DB	Time stamp
1	44	438/197,230,231,289,290,298,301,302,303,305 and (field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/25 15:49
2	19	(field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant) and (gate adj electrode) and (source) and (drain) and (mask with spacer)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/25 15:46
3	11	438/525.ccls. and (field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/25 15:46
4	112	(field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/25 15:47
5	73	(field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant) and @ad<20010716	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/25 15:48
6	33	438/197,230,231,289,290,298,301,302,303,305 and (field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant) and @ad<20010716	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/25 15:50
7	0	438/197,230,231,289,290,298,301,302,303,305 and (field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant) and @ad<20010716 and (implant\$7	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/25 15:51
8	7	438/197,230,231,289,290,298,301,302,303,305 and (field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant) and @ad<20010716 and (implant\$7	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/25 15:51
9	33	438/197,230,231,289,290,298,301,302,303,305 and (field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant) and @ad<20010716 and (implant\$7	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/25 15:52
10	33	438/197,230,231,289,290,298,301,302,303,305 and (field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant) and @ad<20010716 and (implant\$7	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/25 15:54
-	2124	438/197,230,231,289,290,298,301,302,303,305 and (field adj effect adj transistor) and (ion adj implant)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/03 16:16
-	6	438/525.ccls. and (field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/25 15:46
-	85	(field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/25 15:47
-	34	(field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant) and (gate adj electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/20 18:56
-	34	(field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant) and (gate adj electrode) and (source) and (drain)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/21 13:44
-	5	(field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant) and (gate adj electrode) and (source) and (drain) and (lithography)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/20 18:59
-	0	(field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant) and (gate adj electrode) and (source) and (drain) and (pocket adj region)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/10/30 08:59

-	4	438/197.ccls. and (field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/25 15:44
-	27	(field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant) and (gate adj electrode) and (source) and (drain) and (mask)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/20 19:04
-	0	(field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant) and (gate adj electrode) and (source) and (drain) and (mask) and (conductive adj region)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/20 19:05
-	5	(field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant) and (gate adj electrode) and (source) and (drain) and (mask) and (conductive adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/20 19:05
-	6	(field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant) and (gate adj electrode) and (source) and (drain) and (mask) and (conduct\$3 adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/20 19:06
-	18	(field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant) and (gate adj electrode) and (source) and (drain) and (mask with electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/25 15:46
-	12	(field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant) and (gate adj electrode) and (source) and (drain) and (mask with spacer)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/25 15:46
-	1	(field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant) and (gate adj electrode) and (source) and (drain) and (mask with dielectric adj spacer)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/21 15:57
-	0	(field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant) and (gate adj electrode) and (source) and (drain) and (taper with electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/21 16:07
-	0	(field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant) and (gate adj electrode) and (source) and (drain) and (taper\$2 with electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/21 16:11
-	5	(field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant) and (gate adj electrode) and (source) and (drain) and (reduced with electrode)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/21 16:12
-	0	EP-1263027-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/27 08:41
-	2	EP-1263027-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/27 09:04
-	12213048	US 5731239.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/27 08:54
-	2	5731239.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/27 08:57

-	4	512063.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/27 08:58
-	2	5120637.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/27 08:58
-	2	5120673.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/27 09:10
-	0	JP-88317951-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/27 09:23
-	0	JP-2162738-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/27 09:06
-	0	JP-2162738 A-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/27 09:07
-	2	5021355.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/27 09:13
-	2	6501133.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/27 09:15
-	0	2020050621.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/27 09:25
-	0	2000648044.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/27 09:17
-	2	20020050621.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/27 09:18
-	2	5731239.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/27 09:19
-	2	5120673.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/27 09:19
-	1	JP-56048174-\$.did.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/27 09:23
-	2	5021355.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/27 09:25
-	10	438/525,197.ccls. and (field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/06/27 10:11
-	221	mask with (dielectric adj spacer)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/10/30 09:02
-	14806	(advanced adj micro adj devices).asn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/03 16:19

-	42	(advanced adj micro adj devices).asn. and mask and shadow	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/03 16:19
-	10	(advanced adj micro adj devices).asn. and mask and shadow and gate adj electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/03 16:20
-	0	438/519.ccls. and (advanced adj micro adj devices).asn. and mask and shadow and gate adj electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/03 16:21
-	10	(advanced adj micro adj devices).asn. and mask and shadow and gate adj electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/04 10:17
-	0	(advanced adj micro adj devices).asn. and (reduced adj width adj mask) and shadow and gate adj electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/03 16:26
-	0	(advanced adj micro adj devices).asn. and (mask same (reduced adj width)) and shadow and gate adj electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/03 16:28
-	0	(advanced adj micro adj devices).asn. and (mask same reduced same width) and shadow and gate adj electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/04 09:14
-	2	(advanced adj micro adj devices).asn. and (mask same width) and shadow and gate adj electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/04 09:50
-	2	(advanced adj micro adj devices).asn. and (mask same width) and shadow and gate adj electrode and mask	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/04 09:54
-	2	4198250.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/04 09:55
-	6	(advanced adj micro adj devices).asn. and mask and shadow and gate adj electrode and width	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/04 10:38
-	212	(advanced adj micro adj devices).asn. and mask and (gate same width same mask)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/04 10:39
-	212	(advanced adj micro adj devices).asn. and (gate same width same mask)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/04 10:48
-	1	(advanced adj micro adj devices).asn. and (gate same width same mask same implementation)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/04 10:49
-	27	(advanced adj micro adj devices).asn. and (implanting same width same mask)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/04 10:49
-	51	(advanced adj micro adj devices).asn. and (gate same width same mask same implantation)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/04 10:49
-	0	438/525.197.ccls. and (field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/17 08:33
-	0	(inplanting adj ions) same (through adj (conductive adj layer) or (gate adj electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/13 12:15

-	0	(implanting adj ions) same (through adj (conductive adj layer))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/13 12:14
-	0	(implanting adj ions) same (conductive adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/13 12:14
-	1379	(implanting adj ions) same (through adj (conductive adj layer) or (gate adj electrode))	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/13 12:16
-	1243	(implanting adj ions) same (through adj (conductive adj layer) or (gate adj electrode)) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/13 12:16
-	737	(implanting adj ions) same (through adj (conductive adj layer) or (gate adj electrode)) and semiconductor and etching and mask	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/13 12:17
-	551	(implanting adj ions) same (through adj (conductive adj layer) or (gate adj electrode)) and semiconductor and etching and mask and @ad<20010716	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/13 12:19
-	192	(implanting adj ions) near5 (through adj (conductive adj layer) or (gate adj electrode)) and semiconductor and etching and mask and @ad<20010716	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/13 12:19
-	121	(implanting adj ions) near3 (through adj (conductive adj layer) or (gate adj electrode)) and semiconductor and etching and mask and @ad<20010716	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/13 12:19
-	88	(implanting adj ions) near2 (through adj (conductive adj layer) or (gate adj electrode)) and semiconductor and etching and mask and @ad<20010716	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/13 12:35
-	88	(implanting adj ions) near2 (into adj (conductive adj layer) or (gate adj electrode)) and semiconductor and etching and mask and @ad<20010716	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/13 12:56
-	88	(implanting adj ions) near2 (through adj (conductive adj layer) or (gate adj electrode)) and semiconductor and etching and mask and @ad<20010716	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/21 15:15
-	0	implanting adj ions adj through adj conductive adj layer	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/13 14:51
-	1	implanting adj through adj conductive adj layer	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/21 15:10
-	5	implant\$3 adj through adj conductive adj layer	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/21 15:11
-	11	438/525.ccls. and (field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/13 17:38
-	0	438/525,197.ccls. and implant\$3 adj through adj conductive adj layer	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/13 17:37
-	16	438/197,525.ccls. and (field adj effect adj transistor) and (ion adj implant) and (angl\$3 with dopant)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/13 17:38
-	0	438/197,525.ccls. and (implant\$3 adj through adj conductive adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/13 17:40

-	0	5822029.pn. and (black adj substrate)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/14 09:21
-	1	implanting adj through adj conductive adj layer	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/21 15:10
-	0	implant\$3 adj through adj conductive adj layer and (oblique adj angle)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/21 15:13
-	0	implant\$3 adj through adj conductive adj layer and (oblique same implant\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/21 15:14
-	1217	oblique same implant\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/21 15:14
-	3	(implanting adj ions) near2 (through adj (conductive adj layer) or (gate adj electrode)) and semiconductor and etching and mask and @ad<20010716 and (oblique adj angle)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/05/21 15:15

L Number	Hits	Search Text	DB	Time stamp
1	1309	438/197,230,231,289,290,298,301,302,303,305 and (field adj effect adj transistor) and (ion adj implant\$5) and @ad<20010716	USP; US-PGPUB; EPO; JPO; DERWENT	2004/05/25 16:58
2	76	438/197,230,231,289,290,298,301,302,303,305 and (field adj effect adj transistor) and (ion adj implant\$5) and @ad<20010716 and (angl\$3 with dopant)	USP; US-PGPUB; EPO; JPO; DERWENT	2004/05/25 16:59
3	5	438/197,230,231,289,290,298,301,302,303,305 and (field adj effect adj transistor) and (ion adj implant\$5) and @ad<20010716 and (angl\$3 with dopant) and (conductor same	USP; US-PGPUB; EPO; JPO; DERWENT	2004/05/25 17:03
4	4	438/197,230,231,289,290,298,301,302,303,305 and (field adj effect adj transistor) and (ion adj implant\$5) and @ad<20010716 and (angl\$3 with dopant) and (conductor same (ion adj implant\$5)) and mask	USP; US-PGPUB; EPO; JPO; DERWENT	2004/05/25 17:16
5	78	438/197,230,231,289,290,298,301,302,303,305 and (field adj effect adj transistor) and (ion adj implant\$5) and @ad<20010716 and (conductor same (ion adj implant\$5)) and	USP; US-PGPUB; EPO; JPO; DERWENT	2004/05/25 17:17
6	0	438/197,230,231,289,290,298,301,302,303,305 and (field adj effect adj transistor) and (ion adj implant\$5) and @ad<20010716 and (conductor same (ion adj implant\$5)) and mask and (pocket adj regions)	USP; US-PGPUB; EPO; JPO; DERWENT	2004/05/25 17:18
7	11	438/197,230,231,289,290,298,301,302,303,305 and (field adj effect adj transistor) and (ion adj implant\$5) and @ad<20010716 and (conductor same (ion adj implant\$5)) and mask and ((pocket or LDD) adj regions)	USP; US-PGPUB; EPO; JPO; DERWENT	2004/05/25 17:18